

Device Modeling Report

COMPONENTS: Power MOSFET (Professional)
PART NUMBER: SPA11N60C3
MANUFACTURER: Infineon technologies
REMARK: Body Diode (Special)



Bee Technologies Inc.

POWER MOSFET MODEL

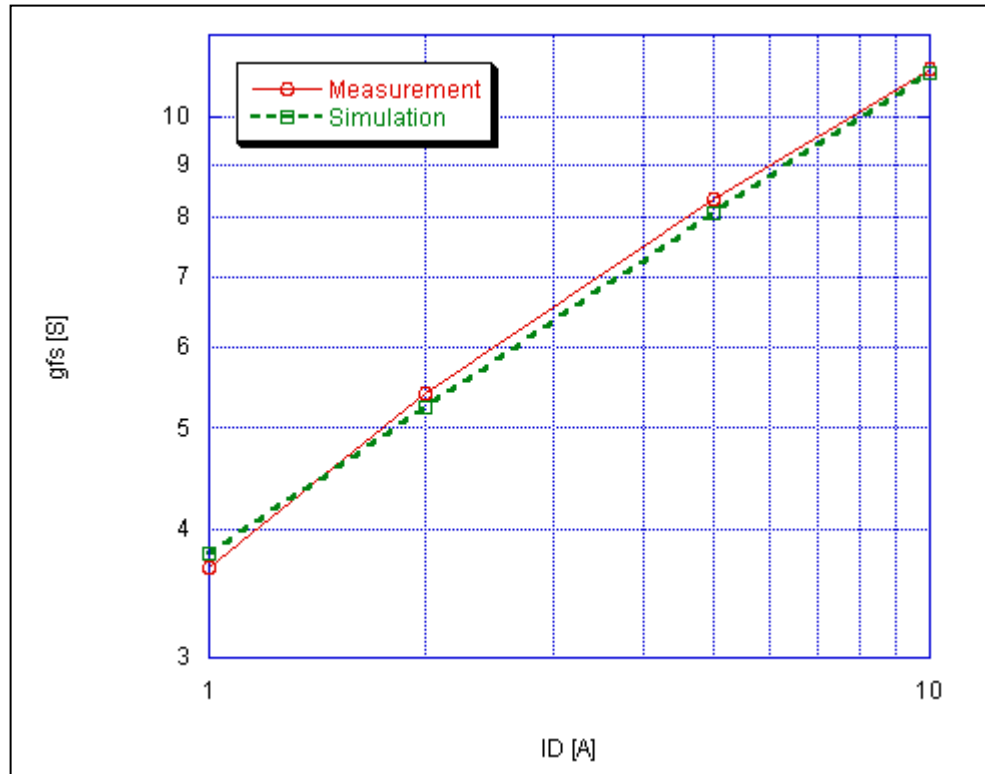
Pspice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Modility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Body Diode Model

Pspice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time

Transconductance Characteristic

Circuit Simulation Result

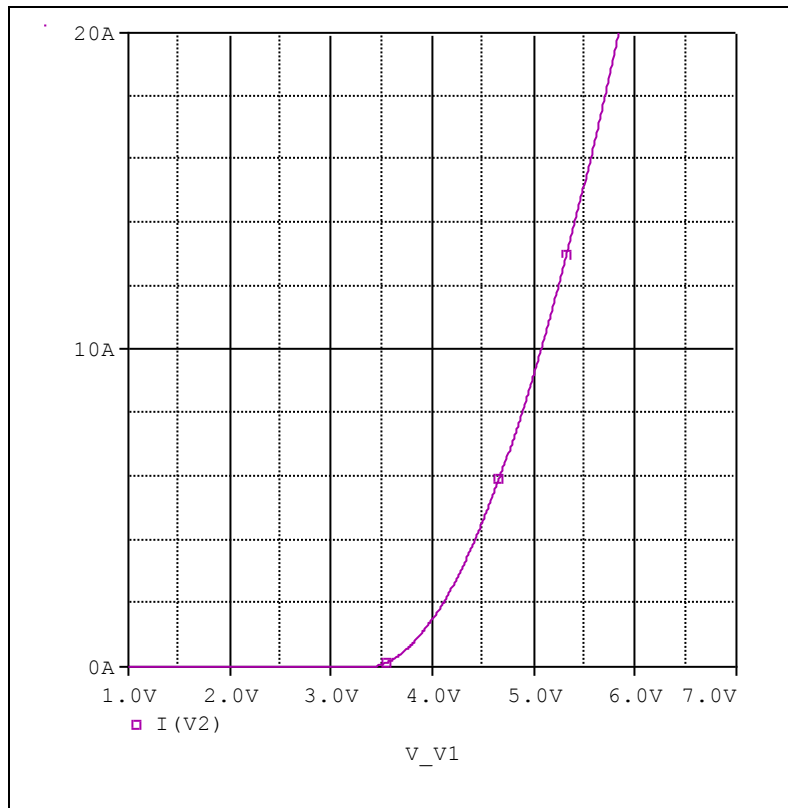


Comparison table

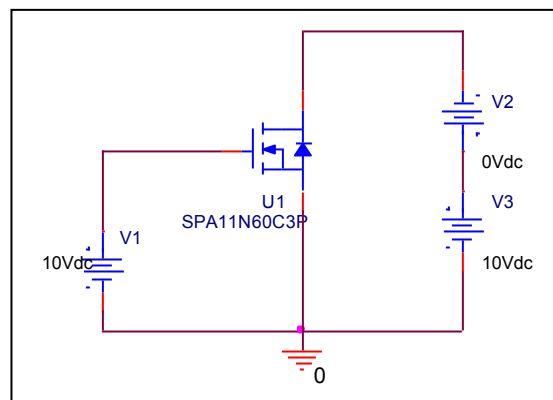
I_D (A)	g_{fs} (S)		Error (%)
	Measurement	Simulation	
1	3.667	3.780	3.081
2	5.400	5.250	- 2.778
5	8.333	8.080	- 3.036
10	11.111	11.050	- 0.549

Vgs-Id Characteristic

Circuit Simulation result

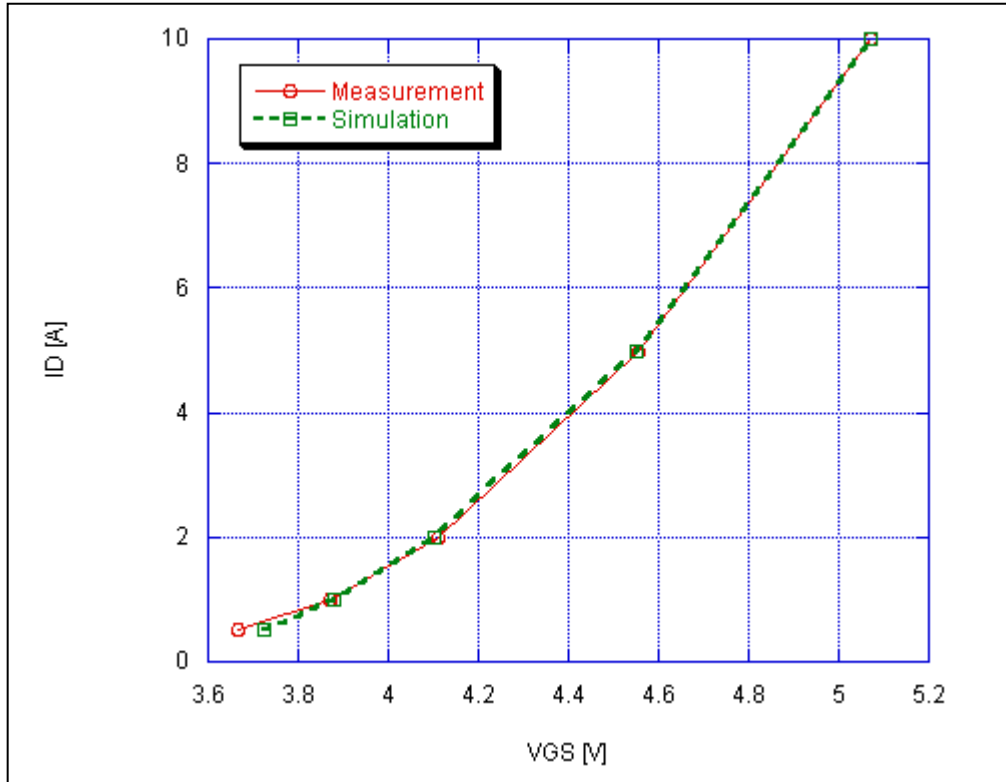


Evaluation circuit



Comparison Graph

Circuit Simulation Result

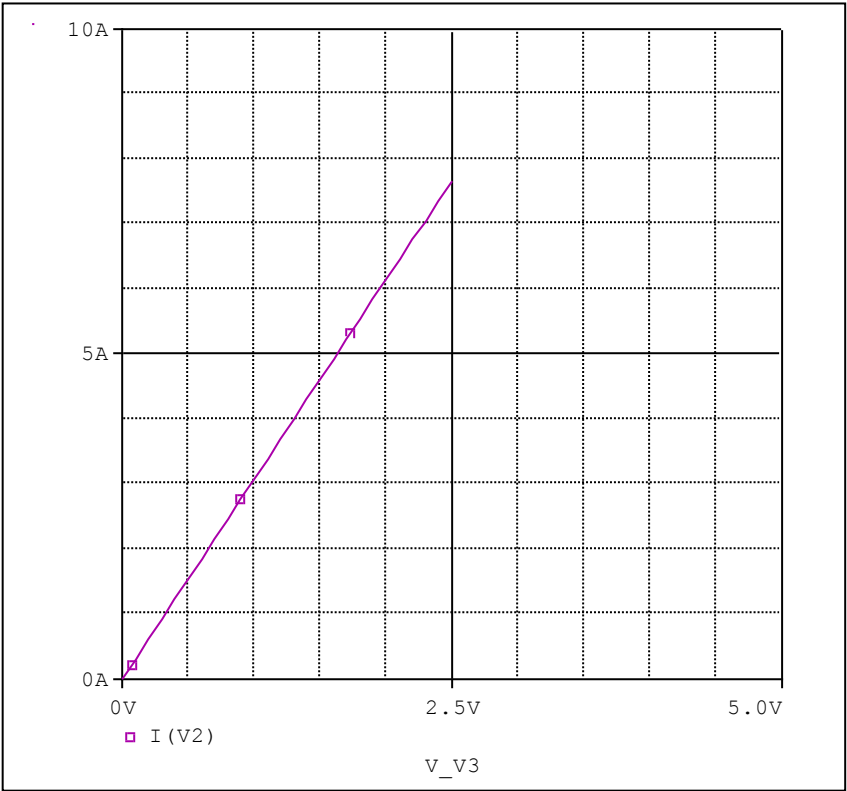


Simulation Result

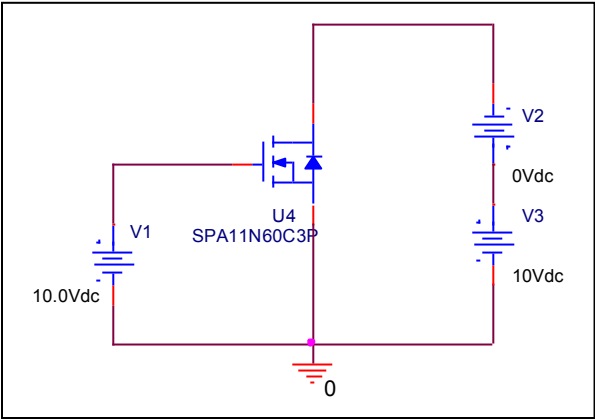
I_D (A)	V_{GS} (V)		Error (%)
	Measurement	Simulation	
0.5	3.665	3.7265	1.678
1	3.870	3.8805	0.271
2	4.110	4.1013	- 0.212
5	4.555	4.5496	- 0.119
10	5.070	5.071	0.020

Id-Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

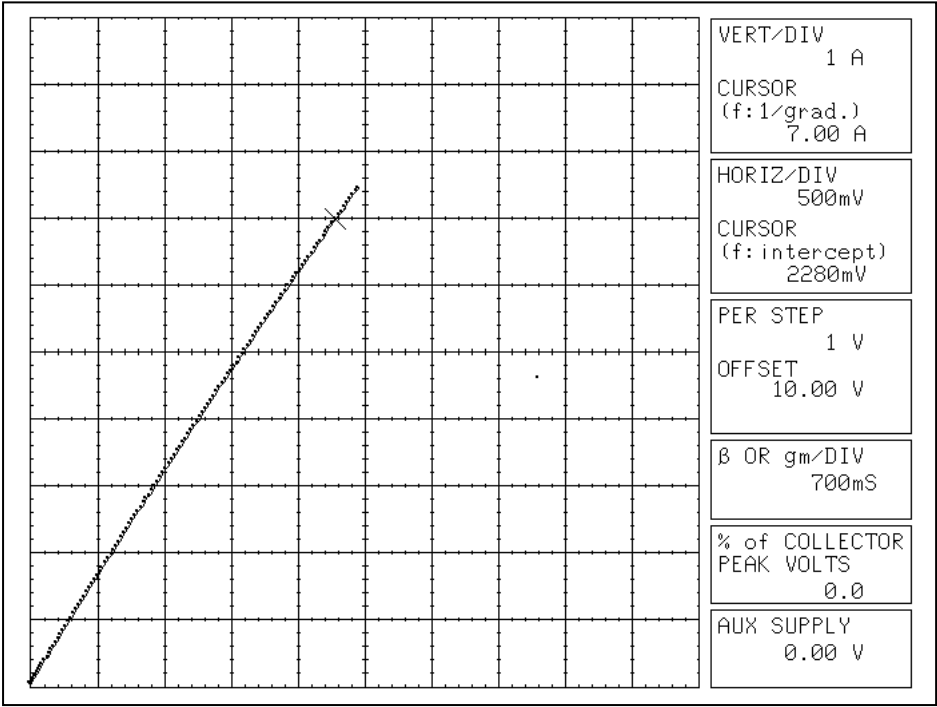


Simulation Result

$I_D=7, V_{GS}=10V$	Measurement		Simulation		Error (%)
$R_{DS} (on)$	0.3257	Ω	0.3257	Ω	0

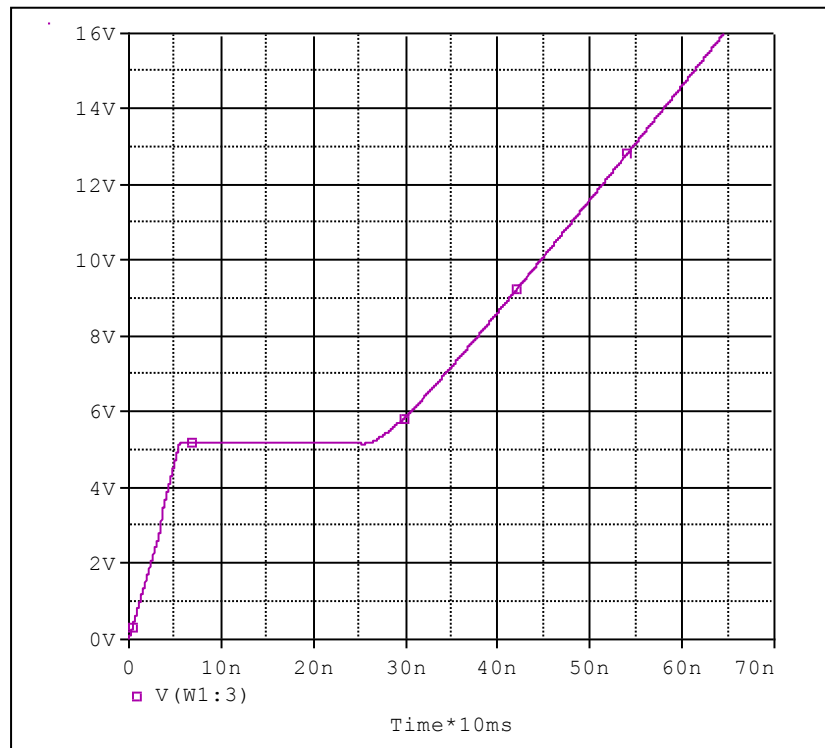
Id-Rds(on) Characteristic

Reference

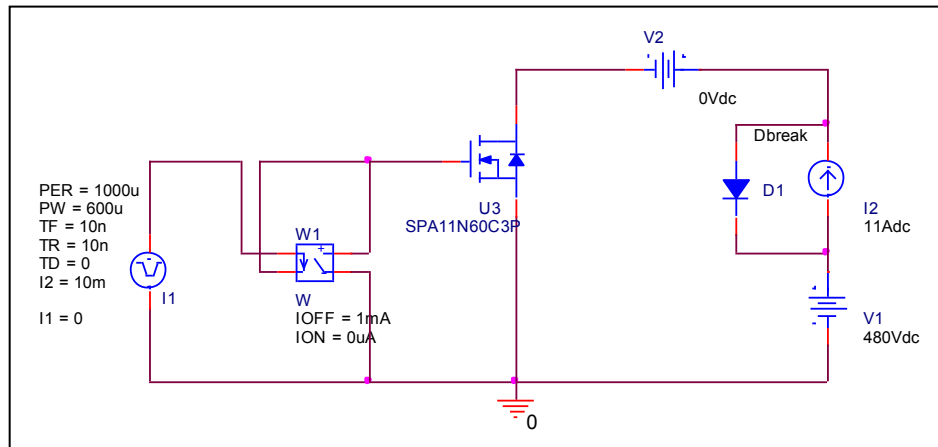


Gate Charge Characteristic

Circuit Simulation result



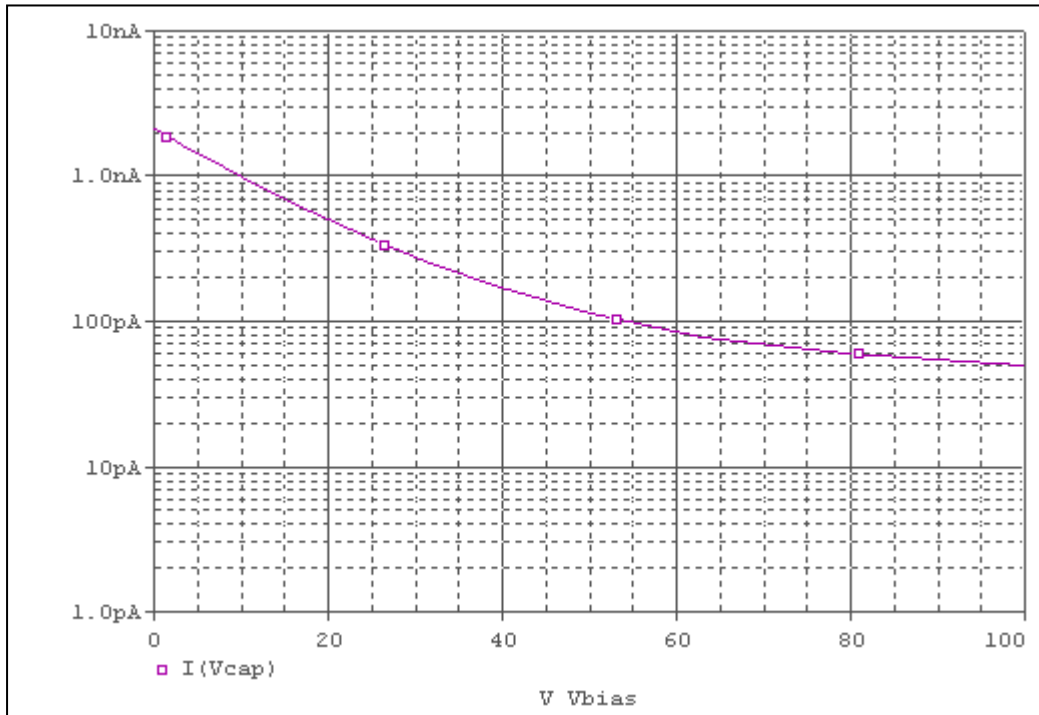
Evaluation circuit



Simulation Result

$V_{DD}=480V, I_D=11A$	Measurement		Simulation		Error (%)
Qgs	5.5	nC	5.55	nC	0.91
Qgd	22	nC	21.59	nC	-1.86
Qg	45	nC	44.70	nC	-0.67

Capacitance Characteristic

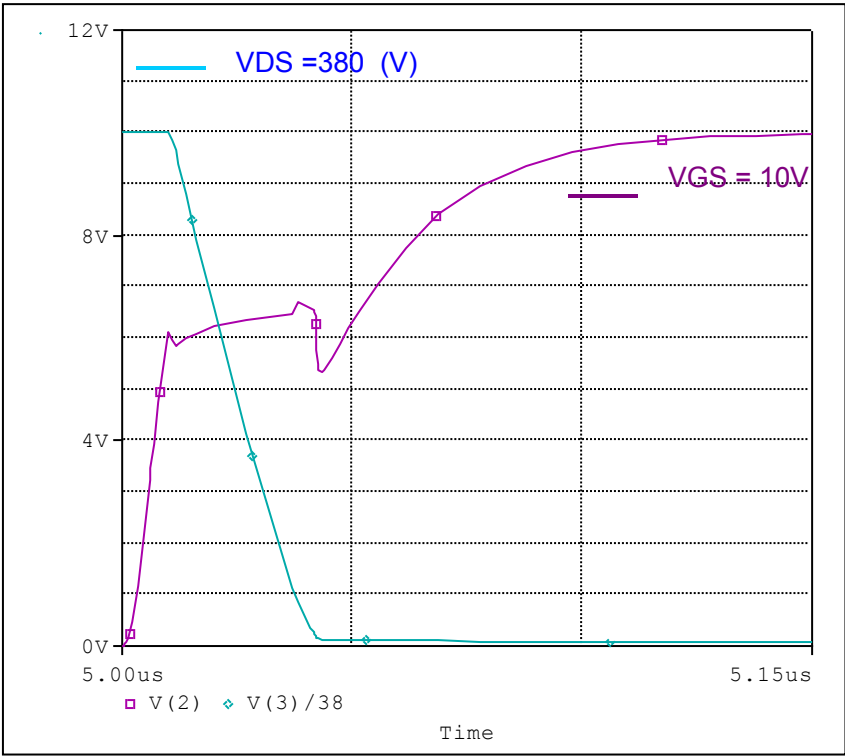


Simulation Result

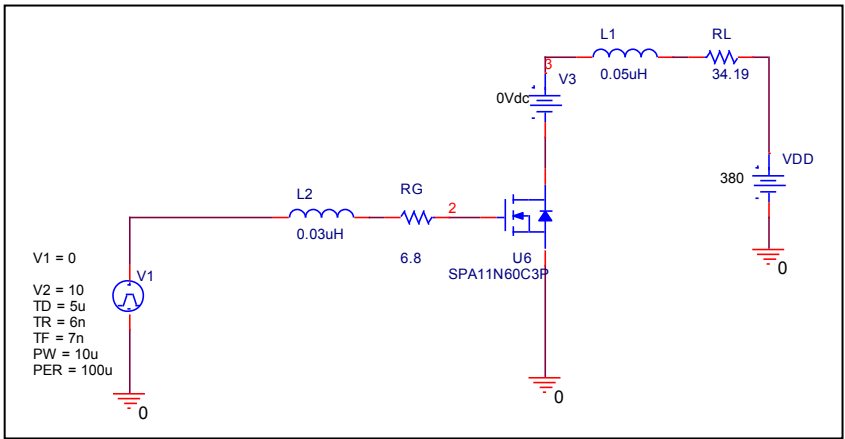
$V_{DS}(V)$	Cbd(pF)		Error(%)
	Measurement	Simulation	
0	2100	2124.000	1.143
10	950	979.042	3.057
25	360	364.959	1.378
50	98.5	103	4.569
100	51	50.494	-0.992

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

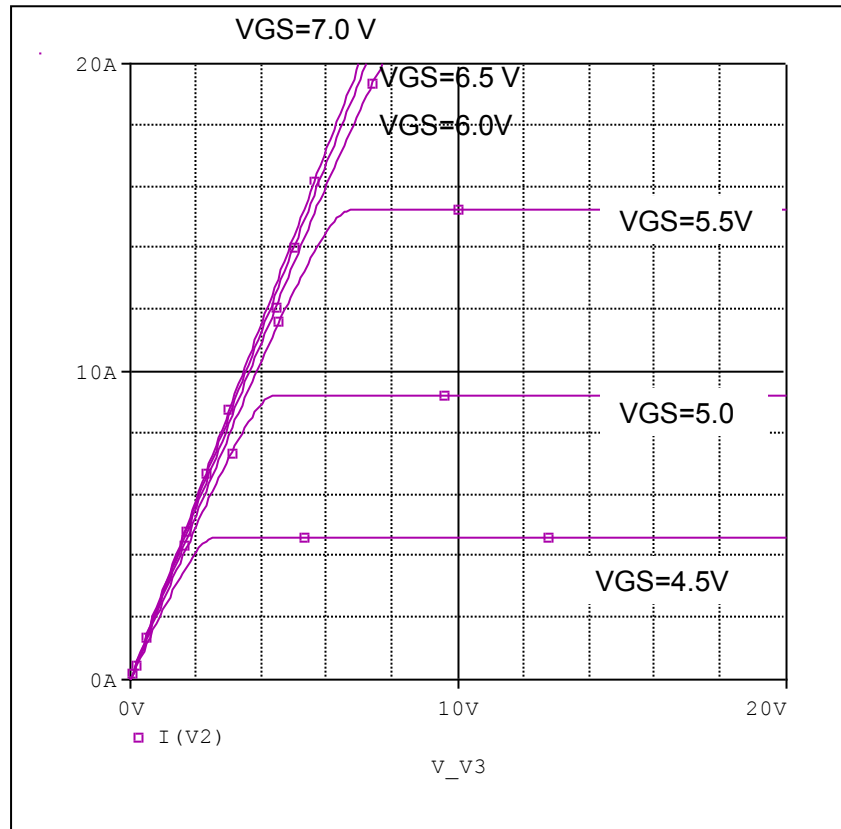


Simulation Result

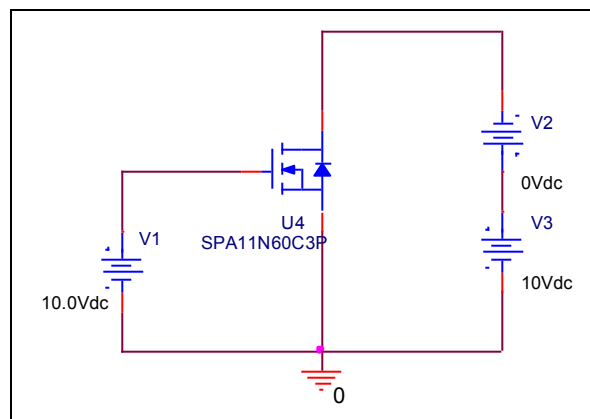
$I_D=11A, V_{DD}=380V$ $V_{GS}=0/10V$	Measurement		Simulation		Error(%)
	td (on)	10 ns	10.002 ns	ns	
					0.02

Output Characteristic

Circuit Simulation result

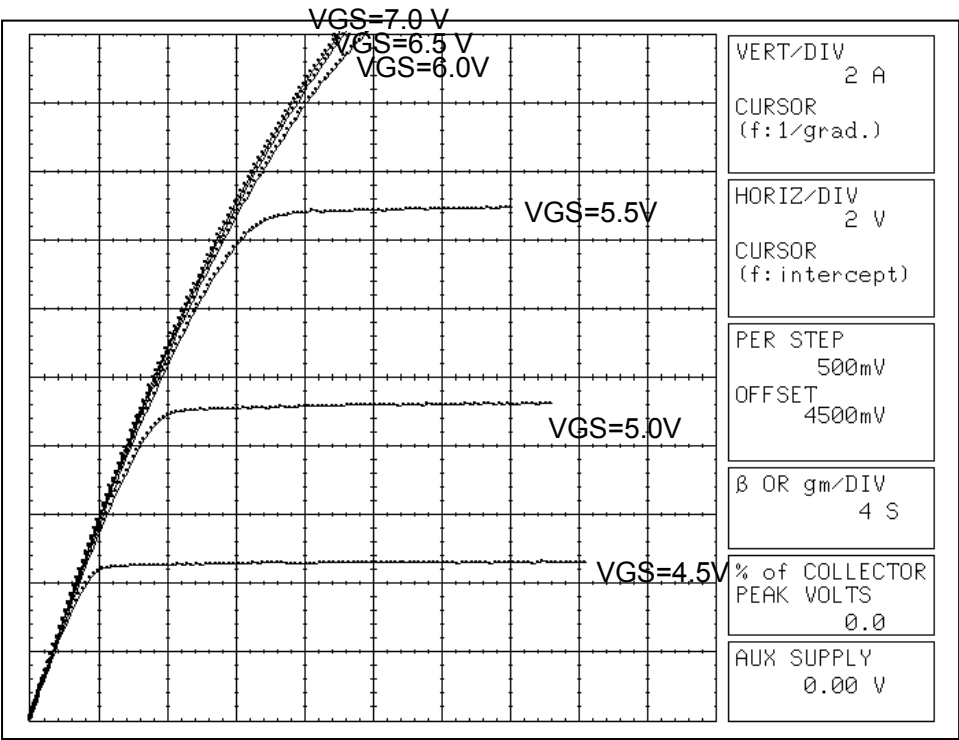


Evaluation circuit



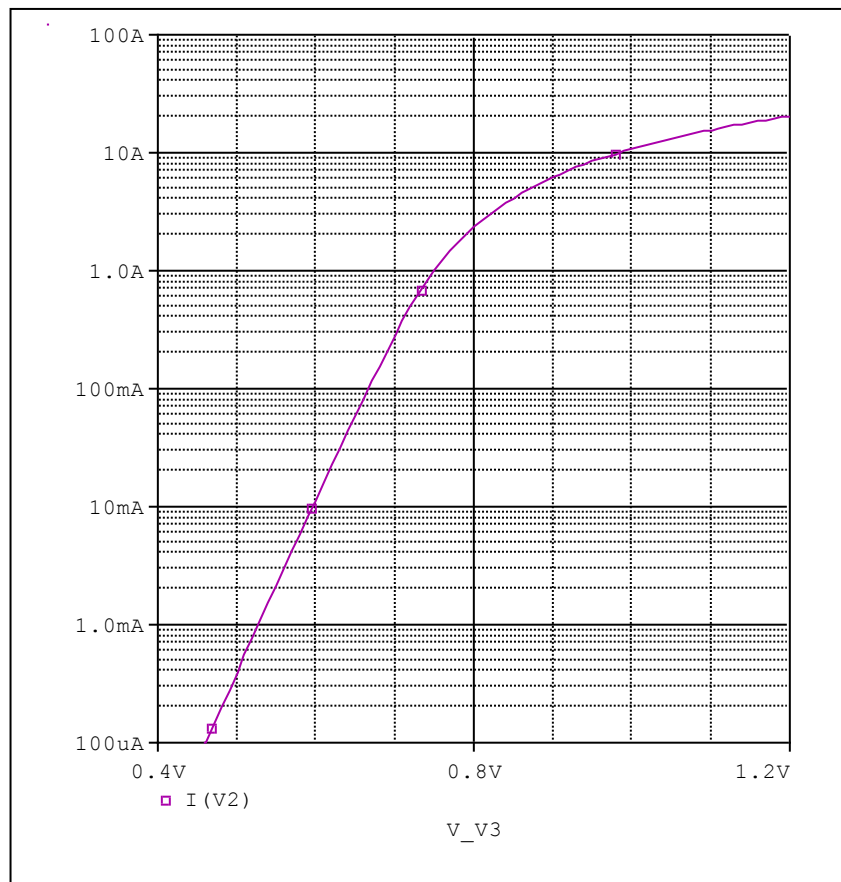
Output Characteristic

Reference

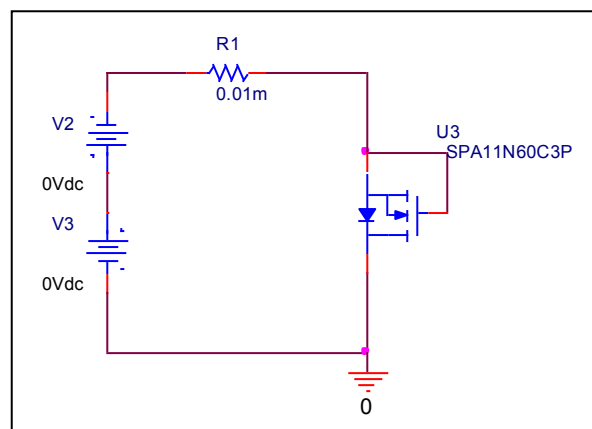


Forward Current Characteristic of Reverse Diode

Circuit Simulation Result

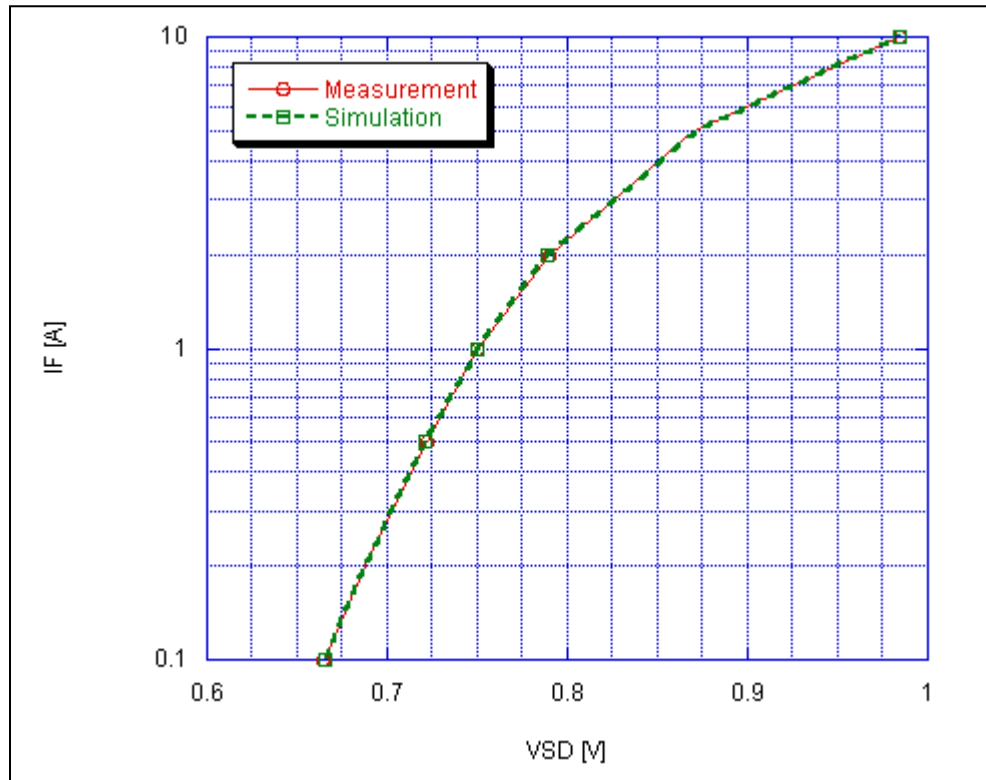


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

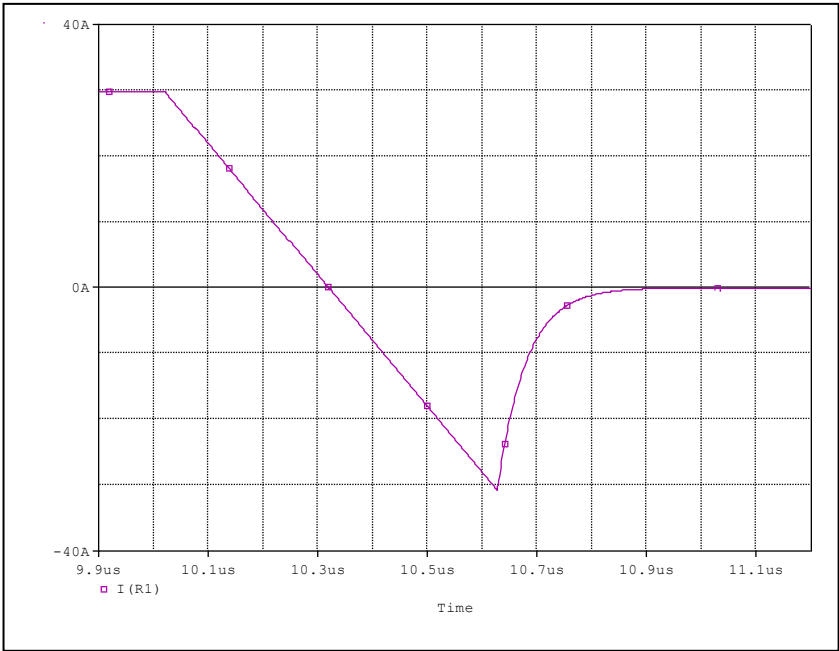


Simulation Result

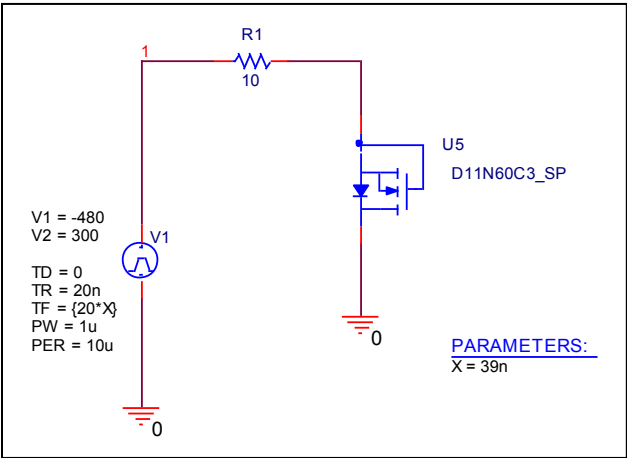
Ifwd(A)	Vfwd(V) Measurement	Vfwd(V) Simulation	%Error
0.1	0.665	0.665685	0.103
0.2	0.688	0.688031	0.005
0.5	0.722	0.720658	- 0.186
1	0.75	0.750378	0.050
2	0.79	0.789318	- 0.086
5	0.87	0.871738	0.200
10	0.985	0.984440	- 0.057

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit



Compare Measurement vs. Simulation
Condition: $di/dt = 100A/\mu s$

	Measurement		Simulation		Error(%)
trr	400	ns	399.395	ns	-0.15